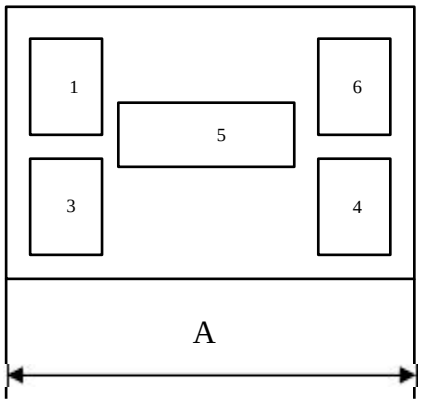
VSP-MIKRON

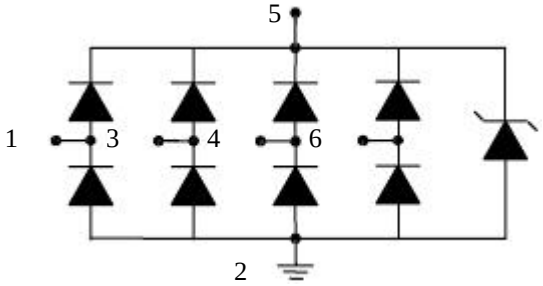
RoHS

Cpecification. Rev. 1 Juli 2011. **KSR- 5.0V4M2.** PRELIMINARY.

Low capacitance TVS Diode **array.**



Pin 2 – Back Side – GND.



Schematic and pinning diagram.

Mechanical date: A_x= 800 um, A_y=480um,
Pad Size for Pin 1, 3, 4, 6 - 85 *100 um.
Pad Size for Pin 5 -250*160 um.
Chip thickness: 138+/-12um.
Scribe Line width - 60um.
Top Metal: Al - for wire bonding.
Back side - Anode: Ti-Ni-Ag for soldering.

Limiting values

Parameter	Symbol	Conditions	Value	Unit
Reverse Stand-off voltage	V_{RWM}	-	5	V
Peak Pulse Power	P_{pp}	t_p=8/20us	150*	W
Peak Pulse Current	I_{pp}	t_p=8/20us	6*	A
Electrostatic Discharge	V_{ESD}	IEC 61000-4-2, level 4.	>8 (Contact); >15 (Air).	kV
Max.junction temperature	T_j	-	+150	ºC

Characteristics (Tj=25ºC)

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{BR}	Breakdown voltage	I_R=1mA	6,0	-	-	V
I_R	Reverse leakage current Pin 5 to 2	V=5V	-		3,0	µA
V_{CL}	Clamping Voltage Any I/O pin to pin 2	I_{pp}=1.0A, t_p=8/20us I_{pp}=6.0A, t_p=8/20us	-	-	15* 25*	V
C_J	Capacitance. Any I/O pin to pin 2	V_R=0 V, f =1MHz	-	-	3,0	pF

*- For Device testing